Electrical control of the hole spin qubit in Si and Ge nanowire quantum dots

Marko Milivojević$^{1,2}$

$^1$NanoLab, QTP Center, Faculty of Physics, University of Belgrade, Studentski trg 12, 11001 Belgrade, Serbia
$^2$Institute of Physics, Pavol Jozef Safárik University, Park Angelinum 9, 040 01 Košice, Slovak Republic

Strong direct Rashba spin-orbit coupling in Si, Ge, and Ge/Si core/shell nanowire quantum dot (QD) allows for all electrical manipulation of the hole spin qubit. Motivated by this fact, we analyze different fabrication-dependent properties of nanowires, such as orientation, cross section, and the presence of strain, with the goal to find the material and geometry that enables the fastest qubit manipulation, whose speed can be identified using the Rabi frequency. We show that QD in nanowires with a circular cross section (cNWs) enables much weaker driving of the hole spin qubit than QDs embedded in square profile nanowires (sNWs). Assuming the orientation of the Si nanowire that maximizes the spin-orbit effects, our calculations predict that the Rabi frequencies of the hole spin qubits inside Ge and Si sNW QD have comparable strengths for weak electric fields. The global maximum of Rabi frequency is found in Si sNW QD for strong electric fields, putting this setup ahead of others in creating the hole spin qubit. Finally, we demonstrate that strain in Si/Ge core/shell nanowire QD decreases the Rabi frequency. In cNW QD, this effect is weak; in sNW QD, it is possible to optimize the impact of strain with the appropriate tuning of the electric field strength.

I. INTRODUCTION

The electron or hole spin trapped inside a semiconductor QD can be used as a building block of a quantum computer [1] [2]. To this end, approaches based on the magnetic [3] [4] and electric [5] [6] fields to manipulate the spin qubit are suggested. Even though the control of the spin qubit is more straightforward with magnetic fields, electrical control of the spin qubit using the electric-dipole spin resonance (EDSR) is favorable in physical realizations [7] [14].

The principal physical mechanism that enables the electrical control of the spin qubit is the spin-orbit interaction (SOC). Besides its positive effect in EDSR based schemes, SOC leads to undesirable effects such as decoherence and relaxation [15] [18]. Among materials with notable SOC that can host spin qubits, Si and Ge have recently attracted much attention due to their free nuclear coherence and relaxation [15–18]. In such systems, the realization of spin qubits with holes rather than with electrons is owed to the fact that SOC is much stronger in the valence than in the conduction bands. The so-called "direct Rashba spin-orbit interaction" (DRSOI) that has been predicted in Ge/Si core/shell nanowires [31] represents an efficient way to manipulate hole spin states in such structures electrically [32] [33]. The other SOC mechanisms, Dresselhaus [34] /Rashba [35], are forbidden by symmetry/much weaker than the DRSOI term.

Here we investigate how the electrical control of a hole spin qubit in Si, Ge, and Ge/Si core/shell nanowire QD is dependent on the electrically tunable DRSOI and fabrication-dependent parameters of the nanowire, such as orientation, cross section, and strain. We focus on realistic profile shapes, circular and square cross sections [36] [37], and realistic profile sizes [38]. Since the hole states in Ge have almost isotropic dispersion relation at the Γ point, we have employed the spherical approximation when studying the hole spin qubit in Ge and Ge/Si core/shell nanowire QD. On the other hand, the orientation dependence of Si hole states is taken into account when discussing the hole spin qubit in Si nanowire QD.

The Rabi frequency, measuring the speed of single-qubit rotations, can be used to assess the efficiency of the hole spin qubit. We have used the fact that the strongest g factor is achieved when the electric and magnetic fields are applied perpendicular to the nanowire and are mutually parallel [30]; the strong driving of the Rabi frequency is enabled by varying the electric field strength. We have divided the Rabi frequency dependence on the electric field strength into two regimes: in the first one, Rabi frequency is proportional to the electric field strength, while in the second regime a nonlinear response is observed. Our analysis shows that hole spin qubits in cNW QDs are much less efficiently controlled by the electric field than in sNW QDs. In the linear regime, we have shown that Rabi frequency in hole spin qubits inside Ge and Si sNW QD are of comparable strength, assuming the orientation of Si nanowire such that the spin-orbit effects are maximized. In the nonlinear regime, the global maximum of Rabi frequency is found in Si sNW QD, putting this setup in favor of others for the creation of the hole spin qubit. We have also investigated the role of strain in hole spin qubit formed in Ge/Si core/shell nanowire QD. We have shown that strain always decreases the Rabi frequency; in cNW QDs this effect is not so pronounced, whereas in sNW QDs the strong impact of shell thickness can be minimized with the appropriate tuning of the electric field strength.

This paper is organized as follows. After the intro-
ductory Section, in Section III the model of the hole spin qubit in Si, Ge, and Ge/Si core/shell nanowire QD is introduced. The numerical procedure used for Hamiltonian diagonalization and the formal definition of the Rabi frequency is given in the same Section. In Sections IV and V dependence of the Rabi frequency on the electric field strength in Si and Ge cNW and sNW QD is analyzed, respectively. Next, in Section VI the role of strain in Ge/Si core/shell nanowire QD hole spin qubit on the Rabi frequency is discussed. Finally, in Section VII short conclusions are given.

II. MODEL

In this Section, we introduce the setup for the creation of the hole spin qubit (see FIG. 1 for an illustration), whose dynamics can be described using the Hamiltonian

$$H = H_{LK} + H_{DRSOI} + H_Z + V + H_{BP}. \quad (1)$$

The first term of the total Hamiltonian $H$ is the four-band Luttinger-Kohn (LK) Hamiltonian [29, 30]. In the simplest case, where the nanowire axes coincide with the crystallographic directions [100], [010], and [001] (xyz orientation), the LK Hamiltonian is equal to

$$H_{LK}^{xyz} = \frac{\hbar^2}{2m} \left[ (\gamma_1 + \frac{5}{2}\gamma_2) \mathbf{k}^2 - 2\gamma_2 (k_x^2 J_y^2 + k_y^2 J_x^2 + k_z^2 J_z^2) \right] - 4\gamma_3 \{\{k_x, k_y\} \{J_x, J_y\} + \{c.p.\} \}, \quad (2)$$

where c.p. stands for cyclic permutation, $\{A, B\} = (AB + BA)/2$ is the anticommutator, $m$ is free electron mass, $\gamma_{1,2,3}$ are the Luttinger parameters, $\mathbf{k}$ is the momentum operator, $J_i$ are spin-3/2 operators obeying the relation $[J_i, J_j] = i\epsilon_{abc}J_c$, ($\epsilon_{abc}$ is the Levi-Civita symbol). Note that in zero magnetic field, momentum operator is equal to $-i\nabla$, while for homogeneous magnetic field $\mathbf{B} = B_x \mathbf{e}_x + B_y \mathbf{e}_y + B_z \mathbf{e}_z$, it equals to $\mathbf{k} = -i\nabla + e/\hbar \mathbf{A}$ ($e > 0$), where the vector potential $\mathbf{A}$ is given as

$$\mathbf{A} = -\frac{1}{2}B_z y \mathbf{e}_x + \frac{1}{2}B_z x \mathbf{e}_y + (B_z y - B_y x) \mathbf{e}_z. \quad (3)$$

It is argued that the strongest spin-orbit effects [30] occur when the nanowire main axis is oriented along the [001] direction, whereas $x$ and $y$ axes coincide with [110] and [110] directions, respectively. In this case, the LK Hamiltonian is equal to [30]

$$H_{LK}^{tot} = \frac{\hbar^2}{2m} \left[ (\gamma_1 + \frac{5}{2}\gamma_2) \mathbf{k}^2 - 2\gamma_2 (k_x^2 J_y^2 + k_y^2 J_x^2 + k_z^2 J_z^2) \right] - 4\gamma_3 \{\{k_x, k_y\} \{J_x, J_y\} + \{k_z, k_x\} \{J_x, J_z\} \} - 2\gamma_2 (k^2 J_y^2 + k^2 J_x^2 + 4\{k_x, k_y\} \{J_x, J_y\}) - 2\gamma_2 (k^2 J_y^2 + k^2 J_x^2 + 2k_z^2 J_z^2). \quad (4)$$

In the case of the Ge nanowire, Luttinger parameters are equal to $\gamma_1 = 13.35$, $\gamma_2 = 4.25$, and $\gamma_3 = 5.69$ [31], while the same parameters for the Si nanowire equal to $\gamma_1 = 4.22$, $\gamma_2 = 0.39$, and $\gamma_3 = 1.44$ [31]. For Ge, the spherical approximation is valid since $\gamma_3/\gamma_2 \approx 1$. Thus, instead of Hamiltonians (2) and (4) we will consider the LK Hamiltonian

$$H_{LK}^{spherical} = \frac{\hbar^2}{2m} \left[ (\gamma_1 + \frac{5}{2}\gamma_2) \mathbf{k}^2 - 2\gamma_2 (\mathbf{k} \cdot \mathbf{J})^2 \right], \quad (5)$$

invariant under arbitrary rotations of the nanowire coordinate system with respect to the crystallographic axes, where $\gamma_s = (2\gamma_2 + 3\gamma_3)/5 = 5.114$.

The second term in Eq. (1) corresponds to the electric field-induced Hamiltonian

$$H_{DRSOI} = -e \mathbf{E} \cdot \mathbf{r} = -e(E_x x + E_y y + E_z z), \quad (6)$$

usually called the DRSOI. Our model neglects the Rashba SOC since it is shown that the DRSOI dominates [30]. On the other hand, Dresselhaus SOC is absent in Ge and Si due to symmetry [42].

Furthermore, the direct coupling of the hole spin to the magnetic field is described through the Zeeman term [42]

$$H_Z = 2k \mu_B \mathbf{B} \cdot \mathbf{J}, \quad (7)$$

with $\mu_B$ being the Bohr magneton, while $k = 3.41 (-0.26)$ [41] is the $g$ factor for Ge (Si) holes. Note that the anisotropic Zeeman term is omitted, being a reasonable assumption in both materials [41].

Next, we describe the QD confinement potential $V$. For a sNW the potential $V$ is equal to

$$V = \begin{cases} 0, & |x| < \frac{L}{2}, |y| < \frac{L}{2}, |z| < \frac{L}{2} \\ \infty, & \text{otherwise.} \end{cases} \quad (8)$$

FIG. 1. Setup for the construction of the hole spin qubit. The main axis of the nanowire coincides with the z-direction. The core of the nanowire has a square (left panel) or circular (right panel) cross section. In the case of the Ge/Si core/shell nanowire, the Si shell around the Ge core increases the overall cross section, where the shell thickness parameter $\gamma = (L_S - L)/L$ is given with the help of the outer Si shell diameter/width $L_S$ and the inner Ge core diameter/width length $L$. Note that no shell is present in the case of the Si and Ge nanowire ($\gamma = 0$). Gating potential $V$ used to localize the hole spin qubit, given in Eqs. (5) and (6) is also denoted. Finally, both the magnetic and electric fields are applied in the x-direction to maximize the spin-orbit effects.
In the xy-plane, hard-wall conditions coincide with the square profile of the nanowire, while the confinement strength \( z_0 \) is dependent on the external gating. In this work, we will assume \( L = 10 \text{ nm} \) and \( z_0 = 30 \text{ nm} \), being typical values in nanowire qubit experiments. Similarly, for a cNW, the gating potential is equal to

\[
V_c = \begin{cases} 
0, & r < R = \frac{L}{2}, \quad |z| < \frac{z_0}{2} \\
\infty, & \text{otherwise},
\end{cases}
\]

where \( r \) represents the radial coordinate and \( R = \frac{L}{2} \) is the half diameter of the profile. The last term in Eq. 1 represents the strain-induced Bir-Pikus Hamiltonian \([14]\), present only in the case of Ge/Si core/shell nanowire. It is equal to

\[
H_{\text{BP}} = -(a + \frac{5b}{4})(\varepsilon_{xx} + \varepsilon_{yy} + \varepsilon_{zz}) + \frac{b(\varepsilon_{xx}J_x^2 + \varepsilon_{yy}J_y^2 + \varepsilon_{zz}J_z^2) + \frac{2d}{\sqrt{3}}(\varepsilon_{xy}(J_x, J_y) + c.p.),}
\]

where \( a, b, d \) are the deformation potentials, while \( \varepsilon_{ij} \) are the matrix elements of the symmetric strain tensor. In strained Ge/Si core/shell nanowires, \( \varepsilon_{xx} = \varepsilon_{zz} = 0 \), \( \varepsilon_{xx} = \varepsilon_{yy} = \varepsilon_{\perp} \). Furthermore, we use the following parameters: \( a = 2eV, b = -2.2eV, d = -4.4eV \) \([15]\). Since the hydrostatic deformation potential \( \alpha \) provides a global shift that can be discarded, the Bir-Pikus Hamiltonian has a very simple effective form \([16]\)

\[
H_{\text{BP}}^{\text{eff}} = |b|(\varepsilon_{\perp}(\gamma) - \varepsilon_{\perp}(\gamma))J_z^2.
\]

In the previous equation, functions \( \varepsilon_{\perp} \) and \( \varepsilon_{\perp} \) depend on the parameter \( \gamma = (L_S - L)/L \), described with the help of the outer Si shell diameter \( D_S \) and the inner Ge core diameter (side length) \( L \). The dependence of \( \varepsilon_{\perp} \) and \( \varepsilon_{\perp} \) on \( \gamma \) and the general discussion of the validity of the model can be found in \([130, 130]\).

As a final remark, it should be noted that there is a global minus sign in Eq. 1. In other words, we assume positive (electron-like) dispersion.

### A. Numerical diagonalization

An adequate basis for the numerical diagonalization is needed to find the eigenvalues and eigenvectors of the hole spin qubit Hamiltonian \( H \). In the case of the hole spin qubit in sNW QD, the eigensolutions will be expanded in the basis set

\[
\langle r|n_xn_yn_z\rangle\langle s|j_z\rangle = \psi_{n_x}(x)\psi_{n_y}(y)\psi_{n_z}(z)\chi_{j_z},
\]

where

\[
\psi_{n}(u) = \frac{2}{\sqrt{L_u}} \sin \left( n\pi \left( \frac{u}{L_u} + \frac{1}{2} \right) \right),
\]

\((n, u) = (n_x/n_y/n_z, x/y/z)\), represents solutions for the particle in the box model, with \( n_{x,y,z} \geq 1 \), \( L_x = L_y = L \), and \( L_z = z_0 \); \( \chi_{j_z} \) represents the eigenvector of the operator \( J_z \),

\[
J_z\chi_{j_z} = j_z\chi_{j_z},
\]

with \( j_z = \pm 3/2, \pm 1/2 \). On the other hand, in the case of the hole spin qubit in cNW QD, the eigenbasis is again adapted to the geometry of the problem and chosen as

\[
\langle r|n_z\rangle\langle s|j_z\rangle = \psi_{(m,n)}^j(r, \varphi)\psi_{n_z}(z)\chi_{j_z},
\]

where \( \psi_{(m,n)}^j(r, \varphi) \) represents the \( \text{th} \) eigenvector of the particle in an infinite circular well \([17]\)

\[
\psi_{(m,n)}^j(r, \varphi) = N(m,n)J_0(m\pi)(\frac{2m\pi}{R})\frac{e^{im\varphi}}{2\pi},
\]

while \( z_{m,n} \) is the \( n \)-th zero of the regular Bessel function \( J_0(z) \) for \( m = 0, \pm 1, \pm 2 \ldots \) quantized values of the angular momentum \( L_z \). Additionally, \( N(m,n) \) represents the normalization constant, set by the equation

\[
N^2(m,n) \int_0^R J_0^2(m\pi)(\frac{2m\pi}{R})rdr = 1.
\]

For sNW QD, numerical diagonalization is done using the 13500 basis states, i.e., the 15 lowest states in each Cartesian direction and four spin states. On the other hand, for cNW QD, in addition to 15 \( \psi_{n_z}(z) \) and four \( \chi_{j_z} \) eigenstates, we have used the 226 lowest \( \psi_{(m,n)}^j(r, \varphi) \) eigenstates of the infinite circular well problem.

### B. Rabi frequency

We assume that qubit states \(+\) and \(-\) correspond to Zeeman split ground hole state. With the applied oscillating electric field \( E_{nw} \) in the direction of the nanowire main axis, we can achieve the electrical control of the hole spin qubit. When the oscillating field is resonant with the Larmor frequency of the qubit, the Rabi frequency, \( \Omega_R \), is equal to

\[
\Omega_R = \frac{e}{\hbar} E_{nw}|(+|z|\rangle|,\]

where \( E_{nw} \) is the strength of the oscillating field. Since the strength of Rabi frequency measures the speed of single-qubit rotations, the value of \( \Omega_R \) for different qubit configurations can be used to access the efficiency of the analyzed hole spin qubit.

The presence of mirror plane symmetries plays an essential role in determining the allowed directions of the electric and magnetic fields for obtaining \( \Omega_R \neq 0 \). Thus, we will shortly discuss their role. First, in zero electric and magnetic field, the system is invariant under three mirror plane symmetries: \( \sigma_{xy}, \sigma_{xz}, \) and \( \sigma_{yz} \). The applied oscillating electric field \( E_{nw} \) in the \( z \)-direction breaks the \( \sigma_{xy} \) symmetry, leaving only two mirror planes as symmetries of the system. If the static electric field is applied in the \( z \)-direction also, the \( g \)-matrix formalism \([45]\) can be used to deduce that Rabi frequency is zero, independently of the orientation of the magnetic field. On
the other hand, the electric field applied in the x- or y-direction breaks $\sigma_{yx}/\sigma_{zx}$ mirror plane, thus lowering the number of mirror plane-symmetries to one only. In this case, Rabi frequency is zero when the magnetic field is applied in the direction perpendicular to the mirror plane [48], whereas in all other cases, nonzero $\Omega_R$ is obtained.

Since $\Omega_R$ is dependent on the $g$ factor strength, it is plausible to set the magnetic and electric field orientation in such a way that the value of $g$ is maximized. This can be achieved when the magnetic field is perpendicular to the nanowire main axis and parallel to the electric field [30]. Thus, in this work we assume that both the electric and magnetic fields are applied in the x-direction of the coordinate frame given in FIG. 1.

### III. HOLE SPIN QUBIT IN SI NANOWIRE QD

We start our analysis of Rabi frequency from hole spin qubits in Si nanowire QD. As discusses earlier, we will focus on the electric field effects, enabled by the presence of DRSOL. For simplicity, we assume that the oscillating electric field strength $E_{nw} = 0.03\text{mV/nm}$ is fixed, as in [49]. Moreover, the study of magnetic field effects is omitted due to the very simple dependence (linear) of $\Omega_R$ on the strength of $B_x$ for reasonably strong fields up to 1T.

In FIG. 2, the dependence of $\Omega_R$ on the electric field strength $E_x$ is plotted for two different orientations of the nanowire and different cross sections, assuming $B_x = 0.1\text{T}$. For weak electric fields, Rabi frequency is linearly dependent on the electric field strength. A signature of the host Si material is the fact that $\Omega_R$ differs significantly for different nanowire orientations, as expected since $\gamma_1/\gamma_2 \gg 1$. LK Hamiltonian $H_{\text{LK}}$ corresponds to the orientation where the spin-orbit effects are the most pronounced [30]; as a comparison, Rabi frequency dependence on $E_x$ for the nanowire orientation that coincides with the main crystallographic axes is given. Also, in FIG. 2 the percentage of light-hole states ($J_z = \pm 1/2$) in the qubit state $|+\rangle$ (very similar result is obtained for $|\rangle$) is given for different cross sections and nanowire orientations. For weak electric fields, $|+\rangle$ is almost exclusively of the light-hole origin, as suggested when analyzing Si nanowire states at the Γ point [30]. However, for stronger fields, the influence of heavy-hole states enhances and can become significant as the electric field strength is further increased.

The response of Rabi frequency to the applied electric field can be divided into two regimes: the first one corresponds to the linear response of $\Omega_R$, whereas in the second regime nonlinear response is present. In the linear regime $\Omega_R$ can be very good approximated as $\Omega_R \approx \alpha_{\text{sup}} E_x$, where the subscript/superscript corresponds to the nanowire profile/orientation. The corresponding parameters $\alpha_{\text{xyz}}^{\text{sup}} = 6.40 \times 10^{-6}\text{MHz m V}$, $\alpha_{\text{xyz}}^{\text{rot}} = 3.26 \times 10^{-5}\text{MHz m V}$, $\alpha_{\text{xyz}}^{\text{rot}} = 5.91 \times 10^{-7}\text{MHz m V}$, and $\alpha_{\text{rot}}^{\text{rot}} = 4.11 \times 10^{-6}\text{MHz V}$ indicate that the square profile is by far more suitable for the electrical control of the hole spin qubit, as well as $z \parallel [001]$, $x \parallel [110]$ orientation. A more complicated dependence on $E_x$ is observed in the nonlinear regime: for both the square and circular profile having the $z \parallel [001]$, $x \parallel [110]$ orientation, global maximum of $\Omega_R$ around $10^4 \text{V/m}$ is observed, followed by the rapid decline of Rabi frequency. On the other hand, for the yzx orientation and both the sNW and cNW QD, $\Omega_R$ is weakly dependent on the electric field strength.

The orbital contribution analysis in each scenario can be used to rationalize the obtained results. Besides the total heavy-hole/light-hole separation that has already been given in FIG. 2, it is possible to match the orbital contribution of heavy-hole/light-hole basis states in qubit states $|+\rangle$. For weak electric fields, an orbital ground state with light-hole spins is dominant ($|11\rangle$ and $|11\rangle$ for Si cNW and sNW QD, respectively.) For stronger fields, other states start to appear as well. Since the

![Graph](image_url)
electric field is applied in the x-direction, it is reasonable to expect that higher orbital states in the x-direction appear in the decomposition of the basis states. As we will show, for weak and moderate electric fields, only a few lowest orbital states with heavy-hole and light-hole spins significantly affect the qubit states. Thus, we will demonstrate that it is possible to approximately describe the Rabi frequency in terms of only a few basis states. In the simplest picture, we can approximate the qubit states as

\[ |+/-\rangle^c \approx c_{11+\pm} |11\rangle |+1/2\rangle + c_{12+\pm} |12\rangle |+1/2\rangle, \]  
\[ |+/-\rangle^s \approx s_{11+\pm} |11\rangle |+1/2\rangle + s_{12+\pm} |12\rangle |+1/2\rangle, \]  

where \( c_{11+\pm}, c_{12+\pm}, s_{11+\pm}, s_{12+\pm} \) are independent on \( x \) purely corresponds to the applied electric field. For stronger fields influence of the other orbital states and heavy-hole spins is evident (see FIG. 3) and it is necessary to expand the number of basis states for realistic approximation of \( \Omega_R \). Plots show that the increased number of basis states gives more realistic results, thus explaining the need for the relatively large number of basis states included in the Hamiltonian diagonalization.

IV. HOLE SPIN QUBIT IN GE NANOWIRE QD

In this Section, using the spherical approximation of the LK Hamiltonian, see Eq. 5, the effect of nanowire geometry and the electric field strength on the Rabi frequency is going to be investigated. Again, we will discuss our results in the magnetic field regime up to 1T, for which the response of \( \Omega_R \) to \( B_x \) is linear.

In FIG. 3, we plot the dependencies of \( \Omega_R \) on the electric field strength for the hole spin qubit in Ge cNW and sNW QD, assuming magnetic field strength \( B_x = 0.1T \). On the right side of the plot, we present the influence of light-hole states in \(|+\rangle\) for the studied cases.

The obtained results can be divided according to the type of response to the electric field. In the linear regime, the fitting \( \Omega_{R_{ii}}^{\text{fit}} = \alpha_i^{\text{Ge}} E_x, i = s, c \), gives the parameters \( \alpha_s^{\text{Ge}} = 3.37 \times 10^{-5} \text{MHz } \mu \text{m} \) and \( \alpha_c^{\text{Ge}} = 1.62 \times 10^{-7} \text{MHz } \mu \text{m} \), confirming the beneficial role of the square profile for the electrical control of the hole spin qubit again. Comparing the results with the hole spin qubits inside Si nanowire QD, the relation \( \alpha_s^{\text{Ge}} \approx \alpha_s^{\text{rot}} \) indicates that both materials can be used to provide similar outputs. The nonlinear regime in Ge differs for different
profiles. In the case of the sNW QD, Rabi frequency is weakly dependent on the electric field strength. In contrast, \( \Omega_R \) in cNW QD gradually increases. However, due to the much stronger slope of \( \Omega_R \) in the linear regime, the hole spin qubit in Ge sNW QD gives much better results than the Ge cNW QD.

To gain better insight into the \( \Omega_R \) difference for Ge cNW and sNW QD hole spin qubit, we analyze the orbital contribution of qubit states in each case of interest. First, we notice that the qubit state \( |+\rangle \) in Ge cNW QD is almost exclusively of light-hole origin for weak electric fields (similar as in Si cNW and sNW QDs, see FIG. 2). In contrast, in Ge sNW QD, the influence of light-hole states is considerably smaller. Besides the different light-hole/heavy-hole influence, the orbital composition of qubit states in cNW and sNW QD differs greatly. In the case of qubit states created in cNW QD, the role of the light-hole \( |11\rangle \) state is dominant for electric field strengths up to \( 1 \times 10^6 \text{ V/m} \). For stronger fields, the influence of orbital \( |21\rangle \) and \( |31\rangle \) states with both light-hole and heavy-hole spins becomes relevant. Similarly as for Si nanowires, we can approximate Rabi frequency behavior with only a few orbital states. In FIG. 5 we compare the obtained numerical results with the linear fit of \( \Omega_R \), minimal model (LH fit \( |11\rangle \)) that approximates qubit states with light-hole states \( |11\rangle \) and \( |12\rangle \), as well as approximations taking into account orbital states \( |11\rangle \), \( |12\rangle \), \( |21\rangle \), \( |22\rangle \), \( |31\rangle \), and \( |32\rangle \) with: a) light-hole (LH fit \( |11\rangle \), \( |21\rangle \), \( |31\rangle \)), b) both the light-hole and heavy-hole spin states (LH-HH fit \( |11\rangle \), \( |21\rangle \), \( |31\rangle \)), as evident from the upper panel of FIG. 5 the minimal model can reproduce the linear response of \( \Omega_R \); for stronger fields, more states are needed to reproduce the Rabi frequency results adequately.

The orbital contribution of Ge sNW QD qubit states is significantly different. For weak electric fields, up to \( 5 \times 10^5 \text{ V/m} \), besides the light-hole state \( |11\rangle \), which is relatively dominant, several other states appear as well. To mention a few, light-hole states \( |12\rangle \), \( |21\rangle \), \( |22\rangle \), \( |31\rangle \), \( |32\rangle \) with light-hole/light- and heavy-hole spins are presented (LH/LH-... |1 2>, |211>).

FIG. 4. For the hole spin qubit in Ge cNW and sNW QD, dependence of the Rabi frequency \( \Omega_R \) on the electric field strength \( E_x \) is given. The applied magnetic field is equal to \( B = (0.1, 0, 0) \text{T} \), while other parameters can be found in the main text. On the right side of the plot, for the configurations studied, the contribution of the light-hole states in the qubit state \( |+\rangle \) versus the electric field strength is given.

FIG. 5. For the hole spin qubits in Ge nanowire with circular (upper panel) and square (lower panel) cross section, comparison between the numerical results, the linear fit of \( \Omega_R \), and the fits of \( \Omega_R \) with approximated qubit states is given. In the case of Ge cNW QD, dashed line represent results when qubit states are approximated with orbital states \( |11\rangle \) and \( |12\rangle \) having light-hole spins; dotted line/dashed-dotted line represent results when states \( |11\rangle \), \( |21\rangle \), \( |31\rangle \), \( |12\rangle \), \( |22\rangle \), \( |32\rangle \) having light-hole/light-hole and heavy-hole spins are used to approximate the qubit states. In the case of sNW QD, besides the linear fit and the numerical results, the minimal fit of qubit states (Eq. 19) is used, as well as approximations based on states \( |111\rangle \), \( |122\rangle \), \( |211\rangle \) with light-hole/light- and heavy-hole spins (see the last paragraph of Section IV).
The effect of strain is such that the orbital contribution of the light-hole state \( |11\rangle \) slightly increases, whereas the light-hole state \( |12\rangle \) decreases more rapidly; thus, it is expected for the Rabi frequency to decrease. However, this decrease is weak, as evident from the fact that \( \Omega_R(\gamma = 0.8)/\Omega_R(\gamma = 0) \) is approximately 1.2 for electric fields up to \( 10^6 \) V/m. On the other hand, in Ge/Si core/shell sNW QD strain has a more pronounced effect, leading to the much stronger decreasing trend of \( \Omega_R \) with the increase of \( \gamma \). As an example, in FIG. 6, the dependence of Rabi frequency on the shell thickness \( \gamma \in (0, 0.8) \) is given for the hole spin qubit in Ge/Si core/shell cNW and sNW QD, assuming electric field strengths \( 10^6 \) V/m and \( 10^4 \) V/m, respectively. It is evident from the plots that strain in sNW QD hole spin qubit leads to one order of magnitude decrease of Rabi frequency, whereas in cNW QD its effect is very weak.

Finally, a weak effect of strain on \( \Omega_R \) in Ge/Si core/shell cNW QD is preserved in the nonlinear regime also. On the other hand, in sNW QD the role of strain is muffled with the increase of the electric field \( (E_x \leq 10^6 \) V/m), reaching the ratio \( \Omega_R(\gamma = 0.8)/\Omega_R(\gamma = 0) \approx 1.35 \) that is comparable with nanowires having a circular profile.

\[
\Omega_R(\gamma = 0) \approx 1.2 \quad \text{for electric fields up to } 10^6 \text{ V/m.}
\]

VI. CONCLUSIONS

We have analyzed hole spin qubits in QD formed inside Si, Ge, and Ge/Si core/shell cNW and sNW. The possibility to electrically control the hole spin qubit through direct Rashba spin-orbit coupling is exploited, and the role of different materials and geometries is investigated in detail, with the goal to find setups that enable the fastest control of the hole spin qubit. The Rabi frequency, the quantity that allows simple estimation of the qubit efficiency, is defined, and its dependence on the electric field strength is investigated. We have shown that the hole spin qubits in QDs inside sNW are much more easily tuned than the corresponding qubits in cNW QDs. For weak fields, Rabi frequency is linearly proportional to the electric field strength. In this regime, we have shown that Rabi frequency in hole spin qubits inside Ge and Si sNW QDs are of comparable strengths, providing that the orientation of Si nanowire is such that the spin-orbit effects are maximized. In the nonlinear regime, the global maximum of Rabi frequency is found in QD inside Si sNW, putting this setup in favor of others for the creation of the hole spin qubit. Finally, we have studied strain effects in the hole spin qubit inside Ge/Si core/shell nanowire QD. Our numerical analysis shows that strain diminishes the Rabi frequency. Whereas in cNW QD this effect is not so pronounced, a strong influence of strain in Ge/Si core/shell sNW QD is observed, such that it can be optimized with the appropriate tuning of the electric field strength.
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